

# P-Channel 30-V (D-S) MOSFET

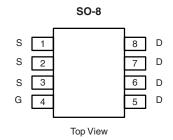
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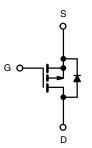
PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$R_{DS(on)}\left(\Omega\right)$	I <sub>D</sub> (A)		
	0.042 at V <sub>GS</sub> = - 10 V	- 5.8		
- 30	0.055 at V <sub>GS</sub> = - 6 V	- 5.0		
	0.060 at V <sub>GS</sub> = - 4.5 V	- 4.4		

#### **FEATURES**

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFET
- Compliant to RoHS Directive 2002/95/EC







P-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATINGS</b>	A = 25 °C, unle	ss otherwise n	oted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V <sub>DS</sub>	- 30		V
Gate-Source Voltage		V <sub>GS</sub>	± 20		
Ocation	T <sub>A</sub> = 25 °C	- I <sub>D</sub>	- 5.8	- 4.1	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 70 °C		- 4.6	- 3.2	
Pulsed Drain Current		I <sub>DM</sub>	- 30		Α
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	- 2.3	- 1.1	
M	T <sub>A</sub> = 25 °C	P <sub>D</sub>	2.5	1.3	W
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C	T FD	1.6	0.8	VV
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Manifestore bounding to Aughing 18	t ≤ 10 s	$R_{thJA}$	40	50	
Maximum Junction-to-Ambient <sup>a</sup>	Steady State	□thJA	70	95	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	$R_{thJF}$	24	30	

#### Notes:

a. Surface Mounted on 1" x 1" FR4 board.



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Parameter	Symbol	Test Conditions	Min.	Typ. <sup>a</sup>	Max.	Unit	
Static					<u>'</u>		
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1.0		- 3.0	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
7 0	_	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$	V <sub>DS</sub> = - 30 V, V <sub>GS</sub> = 0 V		- 1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub> ,	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 70 \text{ °C}$			- 5	μΑ	
o o o o o o o o o o o o o o o o o o o	-	$V_{DS} \le -10 \text{ V}, V_{GS} = -10 \text{ V}$	- 20			Α	
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 5				
		$V_{GS} = -10 \text{ V}, I_D = -5.8 \text{ A}$		0.033	0.042		
Drain-Source On-State Resistance <sup>b</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 6 V, I <sub>D</sub> = - 5 A		0.043	0.055	Ω	
		$V_{GS} = -4.5 \text{ V}, I_D = -4.4 \text{ A}$		0.056	0.060	1	
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 5.8 A		13		S	
Diode Forward Voltage <sup>b</sup>	$V_{SD}$	I <sub>S</sub> = - 2.3 A, V <sub>GS</sub> = 0 V		- 0.8	- 1.1	V	
Dynamic <sup>a</sup>							
Total Gate Charge	$Q_g$			16	24		
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -3.5 \text{ A}$		2.3		nC	
Gate-Drain Charge	$Q_{gd}$			4.5			
Gate Resistance	R <sub>g</sub>			8.8		Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			14	25		
Rise Time	t <sub>r</sub>	$V_{DD}$ = - 15 V, $R_L$ = 15 $\Omega$		14	25		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D\cong$ - 1 A, $V_{GEN}=$ - 10 V, $R_g=$ 6 $\Omega$		42	70	ns	
Fall Time	t <sub>f</sub>			30	50		
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = - 1.2 A, dl/dt = 100 A/μs		30	60		

#### Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. Guaranteed by design, not subject to production testing.

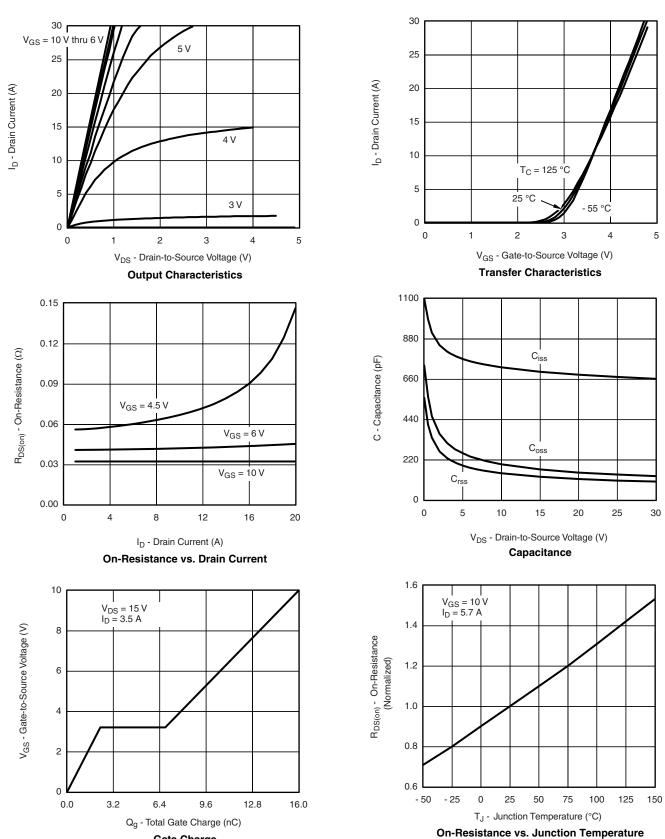
b. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$ 





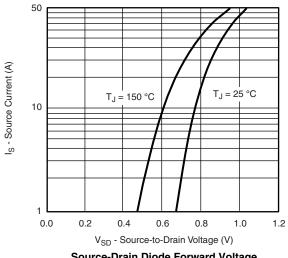
## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

**Gate Charge** 

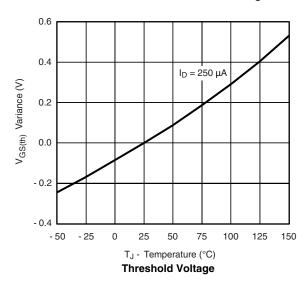




## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

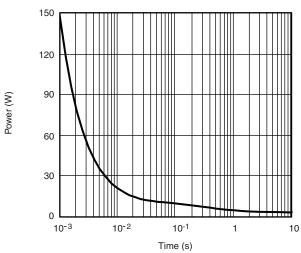


#### Source-Drain Diode Forward Voltage

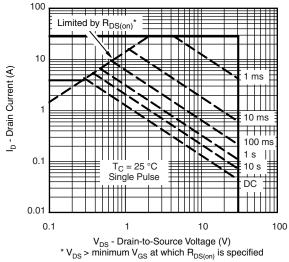


0.20 0.16  $\mathsf{R}_{\mathsf{DS}(\mathsf{on})}$  - On-Resistance  $(\Omega)$  $I_D = 5.8 \text{ A}$ 0.12 0.08 0.04 0.00 0 10 V<sub>GS</sub> - Gate-to-Source Voltage (V)

On-Resistance vs. Gate-to-Source Voltage



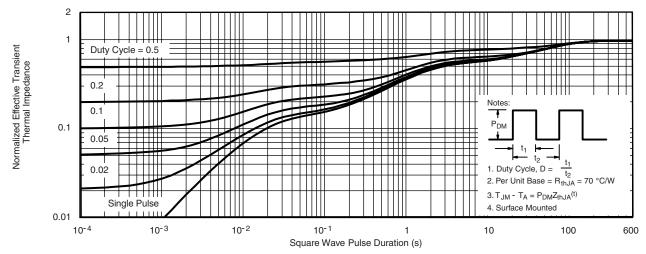
Single Pulse Power, Junction-to-Ambient



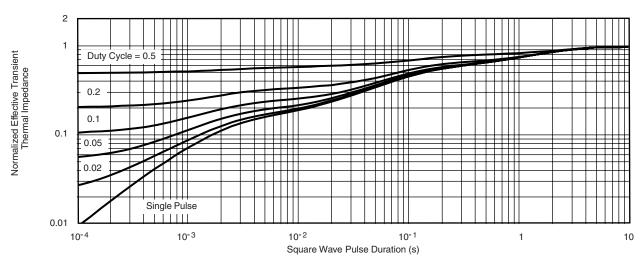
Safe Operating Area, Junction-to-Foot



## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



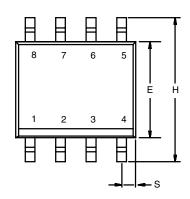
Normalized Thermal Transient Impedance, Junction-to-Ambient

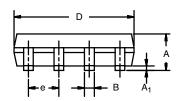


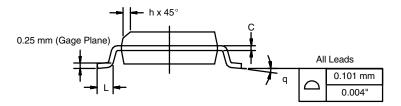
Normalized Thermal Transient Impedance, Junction-to-Foot



**SOIC (NARROW): 8-LEAD** JEDEC Part Number: MS-012





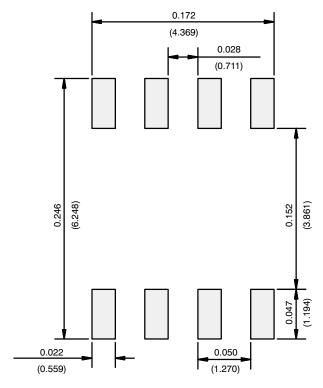


	MILLIM	IETERS	INC	HES		
DIM	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A <sub>1</sub>	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
Е	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050	0.050 BSC		
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Ray I 11-San-06						

ECN: C-06527-Rev. I, 11-Sep-06

DWG: 5498

### **RECOMMENDED MINIMUM PADS FOR SO-8**



Recommended Minimum Pads Dimensions in Inches/(mm)

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